

91-58-7-8/27

Exchange of Experience. The Choice of Impulse for the Load Controller
of a Drum Ball Mill.

mill, examples of the variations of controlling time as a
function of the hydraulic resistance are given. There is
1. diagram and 1 graph.

Card 2/2

1. Ball mills--Operation 2. Ball mills--Electrical controls

THALLIBMAN, S. I.

Report presented at the Conference on Heat and Transfer,
Minsk, USSR, 5-10 June 61.

PH-232
54

253. S. I. VILIMOV, T. I. PERELMAN, Distribution of Charcoal Particles in the Presence of Recombination

254. T. I. PERELMAN, On Heat Transfer in Laminar Flow in the Viscous Part of a Tube

255. I. G. PERELMAN, Solution of Some Problems With Phase Conversions by Operational Calculus

256. I. M. SLEZAK, Numerical Solution of Some Problems of Motion of a Liquid With Variable Viscosity

257. S. I. PERELMAN, On General Transformation of Radiation Fields in Nature

258. Yu. A. SOKOLOVSKII, Calculation of Heating of Rectangular Bodies According to Technological Conditions

259. I. E. MIK, Resistivity of Cylindrical Radiation Fields in Nature

260. V. V. PASHKOV, V. M. KULIKOV, P. B. SOKOLOV, Theory of Penetration

261. I. I. RUMYANTSEV, On Calculation Method of Heat Transfer Through the Interface Between Two Media, On Estimation of the Aggregation State of One or Both Heat Agents

262. A. V. KARANDERYOV, N. A. CHODOROVICH, V. M. KULIKOV, Regularities of Heating of the Contact Surface by Radiation and Convection

263. G. I. BULDISH, Penetration and Some Results of Thermal Treatment of Polyethylene of Non-Uniformly Heated Interface

264. I. S. KLYNOVSKII, Heat and Mass Transfer in a Heat Free and Forced Convection

265. Yu. V. LIPKIN, Heat and Mass Transfer at Turbulent Flow of Compressed Gas as a Precise Substance Supply

266. A. S. GLAZOVSKY, Z. E. SOLODOV, Influence of Mechanical Curvature and the Surface on Heat Transfer Rate of Radiosurgical Solder

267. A. A. GORENSTEIN, On the Heat and Mass Transfer Theory at Convective Motion of Liquid

268. V. I. SABOROV, N. K. DRAGOVICH, B. I. SOKOLOV, Measurements of Temperature Turbulent Pulselets in a Liquid Flow

269. A. A. ROMASHOV, On the Theory of Dusion and Penetration of a Body (The Stephan Problem)

TAUBMAN, YE. I.

"Method of estimating heat-exchange through the wall during changes in the state of aggregation of one or both heat conductors."

Report presented at the 1st All-Union Conference on Heat- and Mass- Exchange, Minsk, BSSR, 5-9 June 1961

TAUBMAN, Ye.I.i. MAL'TSEV, M.L.

Selecting the optimum parameters of spray drying processes in the production of powdered dried vegetables. Izv.vys.ucheb.zav.; pishch. tekhn. no.3:106-108 '62. (MIRA 15:7)

1. Ukrainskiy nauchno-issledovatel'skiy institut konservnoy promyshlennosti.
(Vegetables—Drying)

TAUBMAN, Ye. I.

Improved method of thermal calculation of evaporating systems.
Izv. vys. ucheb. zav.; pishch. tekhn. no.5:120-126 '62.
(MIRA 15:10)

1. Ukrainskiy nauchno-issledovatel'skiy institut konservnoy
promyshlennosti.

(Evaporating appliances)
(Heat—Transmission)

TAUBMAN, Ye.I., inzh.

Concerning the classification of simulation methods. Izv. vys.
ucheb. zav.; energ. 5 no.7:116-118 Jl '62. (MIRA 15:7)

1. Ukrainskiy nauchno-issledovatel'skiy institut konservnoy
promyshlennosti.
(Models and modelmaking) (Electromechanical analogies)

34661

S/096/62/000/002/005/008
E140/E135

26.5.200

AUTHORS: Liberman, I.G., and Taubman, Ye.I.

TITLE: The calculation of convection heat exchange on
electronic analogue computers

PERIODICAL: *Teploenergetika*, no. 2, 1962, 67-70

TEXT: The article describes the solution of an empirical
equation for convection heat exchange:

$$y = cx_1^{n_1} \cdot x_2^{n_2} \cdots x_k^{n_k} \quad (1)$$

where c is a constant, x_i are variables defining the heat
exchange process (heat transfer factor, rate of circulation of
heat carrier, geometrical dimensions and form, etc.), and the
 n_i are real numbers. The problem was set up for the Soviet
Analogue Computer MH-7 (MN-7) according to the block diagram of
Fig. 1. Here the blocks in the extreme left-hand column are the
sources of the variables x_i , the blocks of the second column
are nonlinear elements (function generators) for obtaining the

Card 1/3

The calculation of convection heat... S/096/62/000/002/005/008
E140/E135

logarithm of the variable, the blocks in the third column are multipliers, yielding the products of the respective exponents with the logarithms, the next to the last block is a summation unit, and finally, the output y is taken from a nonlinear unit yielding the antilog. The article further discusses the modification of a piecewise-linear diode function generator to make the functions log, antilog easier to generate. Scale factors and error are discussed. As an example, the heat transfer coefficient in the heating of water in a round pipe (average temperature 80 °C) was calculated on the machine MN-7 as a function of the speed of the water and the pipe diameter. For this simple equation

$$\alpha = 0.023 B \frac{w^{0.8}}{d^{0.2}} = B' \frac{w^{0.8}}{d^{0.2}} \quad (10)$$

a circuit with eight operational amplifiers was required (and three function generators) with an estimated error not exceeding 3%. The article concludes with a plea for wider use of analogue computers for heat transfer calculations.

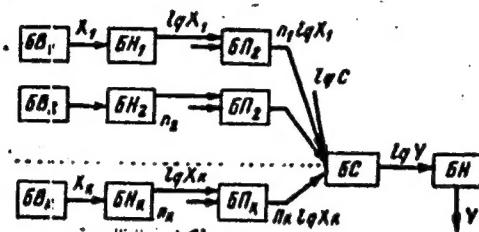
Card 2/3

The calculation of convection heat ... S/096/62/000/002/005/008
E140/E135

There are 6 figures, 2 tables and 5 Soviet-bloc references.

ASSOCIATION: PKI Pishcheprom - UkrNIKIP

Fig.1



Card 3/3

MAL'TSEV, M.L.; TAUBMAN, Ye.I.; SHMUKLER, A.S.

Operation conditions of the spray dryer in the processing of
powdered vegetables. Kons.i ov.prom. 17 no.5:22-24 My '62.

1. Ukrainskiy nauchno-issledovatel'skiy institut konservnoy
promyshlennosti.

(MIRA 15:5)

(Vegetables--Drying)

TAUERMAN, Ye.I.

Transient processes in a multistage evaporation apparatus
for the production of tomato paste. Izv. vys. ucheb. zav.;
pishch. tekhn. no.6:82-87 '63. (MIRA 17:3)

1. Ukrainskiy nauchno-issledovatel'skiy institut konservnoy
promyshlennosti, otdel mekhanizatsii i avtomatizatsii.

MAL'TSEV, M.L.; TAUBMAN, Ye.I.

Determining the size of the drop of the atomized product in spray drying in the manufacture of powdered vegetables. Kons. i ov.prom. 18 no.3:23-24 Mr '63. (MIRA 16:3)

1. Ukrainskiy nauchno-issledovatel'skiy institut konservnoy promyshlennosti
(Vegetables--Drying)

TAUBMAN, E. I.

"Application of continuous electronic computers for the calculation of heat exchangers and evaporators."

report submitted for 2nd All-Union Conf on Heat & Mass Transfer, Minsk,
4-12 May 1964.

Ukraine Sci Res Inst of Starch & sugar Industry.

TAUBMAN, Ye.I., inzh.

Simulation of the transient operation of a multistage evaporating system using an electronic computer. Izv. vys. ucheb. zav.; energ. '7 no.5:73-80 My '64. (MIRA 17:7)

1. Ukrainskiy nauchno-issledovatel'skiy institut konserinoy promyshlennosti.

TAUBNER, Robert, tudományos munkatárs

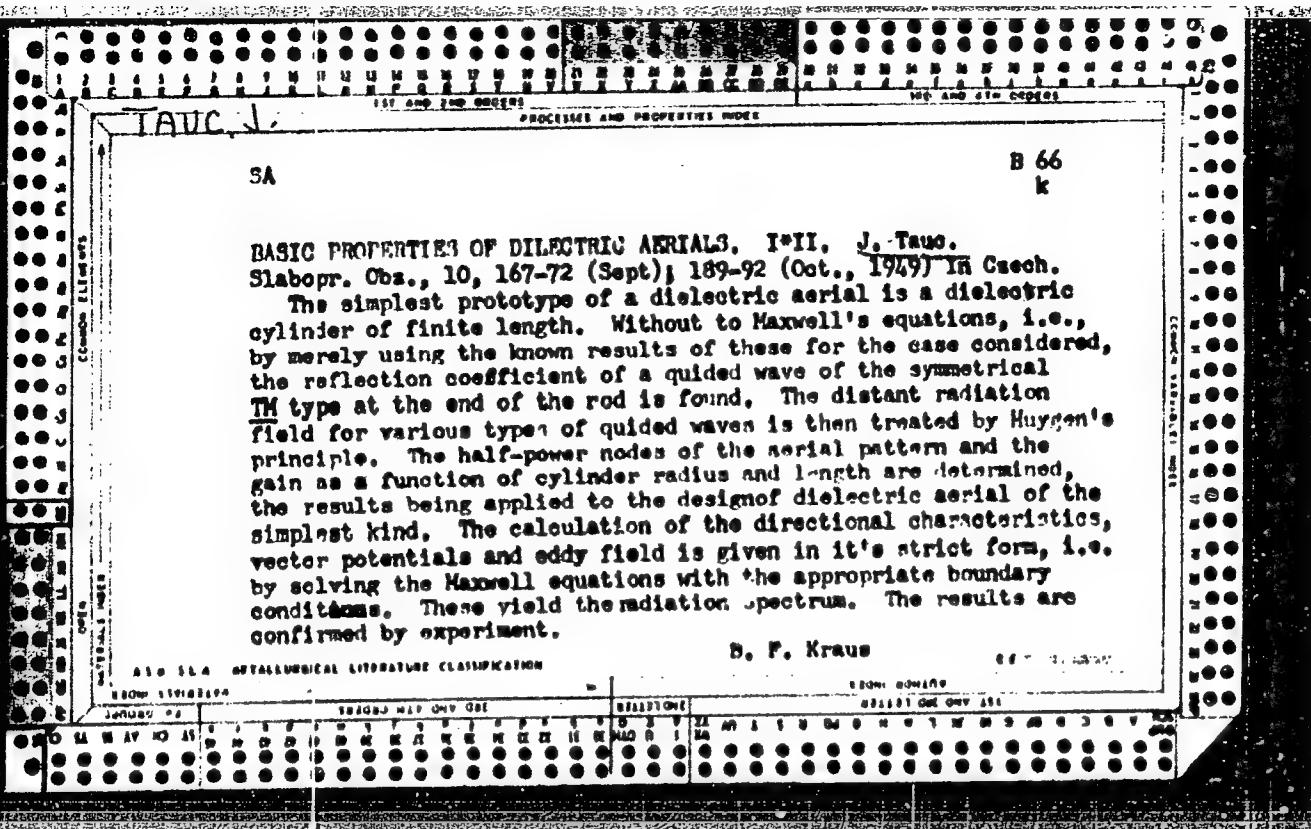
Method for testing the economy of air heating in case of
surface (recuperative) air heaters with special regard to
low temperature corrosion. Ipari energia 4 no.11;246-251
N '63.

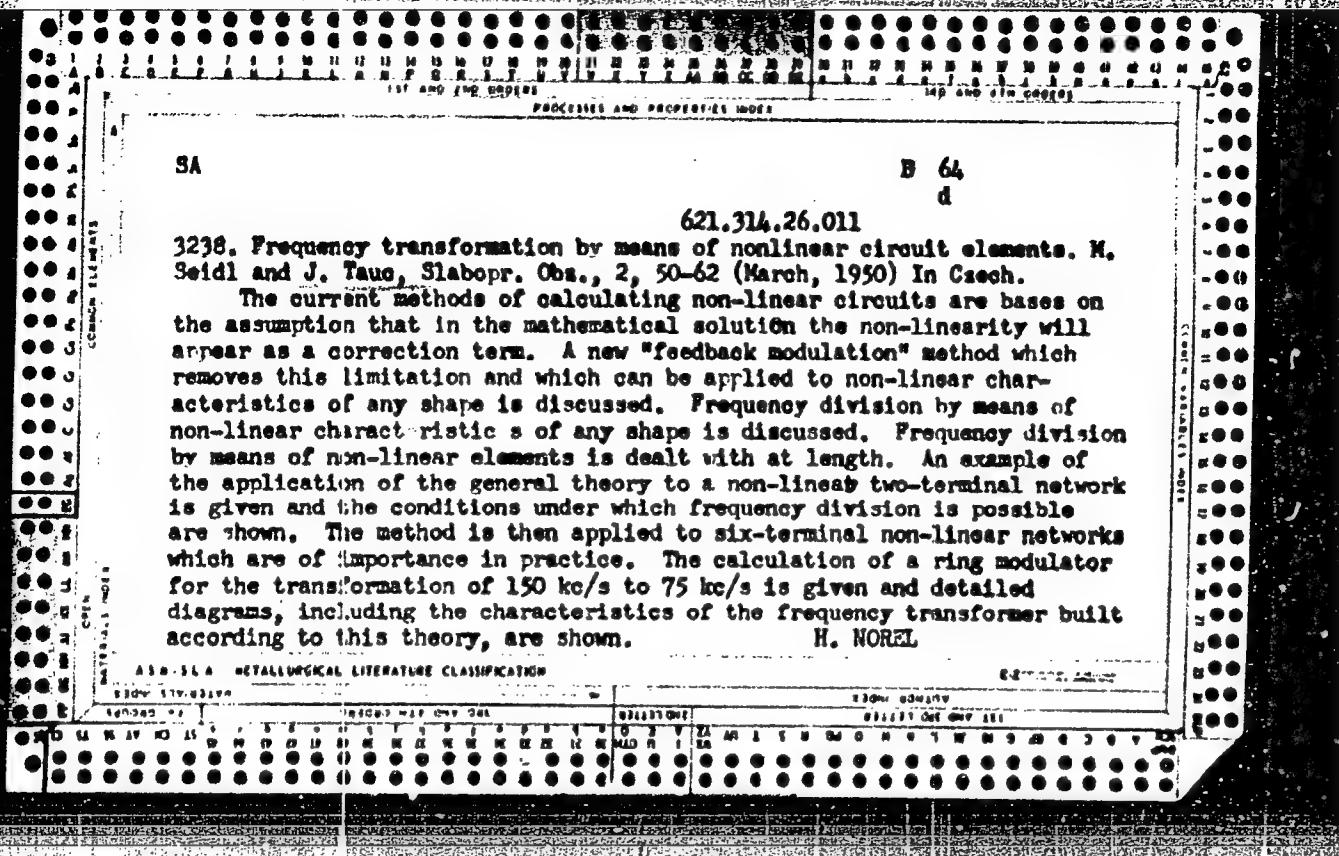
1. Research Institute of Heat Engineering, Budapest.

TAUBWURCEL, Z.

"Intrafactory accounting." p. 91. (ODZIEZ, Vol. 4, no. 3, Mar. 1953, Lodz, Poland)

SO: Monthly List of East European Accessions, L. C., Vol. 3, No. 5, May 1954, Uncl.





TAUC, J.
S. K.

Lines, Networks, Waveguides,
Filters

B 66

A

621.392.2 : 621.3.011

274. Wave amplification in a non-linear medium.
J. TAUC. *Slabov. Obs.*, 12, 2-7 (Jan., 1951) *In*
Czech.

In a medium the dielectric constant of which is a function of the electric field a transfer of energy can take place between two electromagnetic waves. The conditions are discussed under which use can be made of this effect for the amplification of a travelling electromagnetic wave by an auxiliary wave of double its frequency travelling in the same non-linear medium. The resulting gain is calculated and it is shown that the phase angle between the two waves in a sufficiently long line becomes automatically such that the energy transfer is a maximum. For a given length of line the amplification in db is $\propto 1/\lambda$ (wavelength). The effect can be used for amplification as well as mixing and the advantage over other methods is a relatively low noise level.

H. NORELL

for 12

TAUC, J.

537.323 : 537.311.33

CZECH

6635. The effect of thermal emission of holes on the thermal e.m.f. of n-type semiconductors. J. TAUC AND Z. TROUSIL, Czech. J. Phys., 3, No. 2, 121-3 (1953) *In Russian.*

On measuring the thermal e.m.f. of n-type semiconductors, it was observed that the character of the dependence on the temperature was different when using a cold point and a heated flat electrode from that when using two flat electrodes. This effect can be explained theoretically by the following conception. Under the point electrode a large temperature gradient is created which, due to the diffusion of holes from the warmer parts, causes a greater concentration of the current carriers in the cooler parts than corresponds to the equilibrium value. The potential barrier under the point prevents the electrons from entering the contact but does not prevent the penetration of the holes. The excess of holes causes an electric voltage analogous to that in a barrier layer cell. On the assumption that most of the temperature gradient occurs at a distance which is small compared to the diffusion distance of the holes, that the temperature gradient between the surface of contact of the tungsten point and the sphere of radius r_s is negligible and that the concentration of the holes compared to the concentration of n-type impurities is small, an expression was derived for the additional voltage ΔU caused by the excess of holes. Within the limits of validity of the derived theory, i.e. for lower temperatures, quantitative agreement was obtained with experiment. For higher temperatures the measured curve always lies below the theoretical. A possible explanation is that the potential barrier loses its efficiency at higher temperatures, a fact supported by measurements made at high temperatures. BB 4

Institute of Tech. Physics,
Prague

TRANSC.

CZECH

537.311.33 : 537.32 : 621.314.7

6274. An explanation of some anomalous thermo-electric phenomena on the surface of transistor materials. J. TAUC. Letter in Czech. J. Phys., 3, 259 (Sept., 1959).

The anomalous surface layer reported by Tauc and Hogař in 1958 [ibid. 3, 259 (1959)] is explained by a self-consistent determination of the band structure of the surface layer. The theory, using the theory of Hückel Kondo [ibid. 3, 259 (1959)], predicts a surface layer of opposite conductivity type to the reversal of thermo-e.m.f. of a point contact on warming up; the crystal may be explained on the basis of a theory due to Tauc and Troubil [Abstr. 6615 (1954)].

60 C. A. HOGARTH

TRAJECT
CZECH

537.323 : 537.311.31

✓ 6636. The theory of the thermal e.m.f. of semi-conductors. J. TAUC. Czech. J. Phys., 3, No. 4, 282-303 (1953).

After a discussion of the present theory of the thermal e.m.f. of semiconductors, the theory is extended to non-homogeneous semiconductors. Its relationship to thermodynamics is discussed and it is then applied to the study of the influence of potential barriers. Further cases are discussed in which the velocity or the concentration of electrons does not conform to a state of thermal equilibrium as in the case of diode-type barriers or for injected current carriers. The results are applied to a discussion of the influence of high temperature gradients. The influence of minority current carriers on thermal e.m.f. is systematically treated. Equations are derived and the magnitudes of certain anomalous effects are estimated. Some of these have not yet been experimentally observed

BB AM A

TAUC, J.

C Z È C H

6613. A method for the precise measurement of
thermal ~~conduct~~^{conduct} of samples with great thermal con-
ductivity. J. TAUC, J. BEGNAU AND A. ABRAHAMS.
Letter in Czech J. Phys. L, Vo. 4, 314-15 (1953). In
Russia.

Describes an apparatus in which the two ends of a
specimen of the material under investigation (semicon-
ductors are suggested) can be kept at precise and
known temperatures. No experimental results

537.32
J. M. HALL

623.314.53
4613. Germanium rectifiers of the $p-n$ type. I. T. T. Elektrotech. Obozor, 42, No. 9, 495-8 (1953) *By C. C. H.*
A review of junction-type Ge rectifiers. The principle of a $p-n$ junction is briefly explained, and the properties of a h.v. rectifier described by Pietropol [Phys. Rev., 81, 126 (1951)] and those of a General Electric G-10 power rectifier are discussed. Extraction and diffusion methods of producing $p-n$ junctions are briefly mentioned
2 1. 10000 TC2

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APPROVED FOR RELEASE: 07/16/2001

CIA-RDP86-00513R001755120009-1"

TAUC, J.

"Method of Photoelectric Line for Internal Photoeffect" P. 99
(CESKO-SLOVENSKY CASOPIS PRO FYSIKU Vol. 4, No. 1, Feb. 1954 - Praha, Czech.)

SO: Monthly List of East European Accessions, (EEAL), LC., Vol. 4, No. 4,
April 1955, Uncl.

"APPROVED FOR RELEASE: 07/16/2001

CIA-RDP86-00513R001755120009-1

APPROVED FOR RELEASE: 07/16/2001

CIA-RDP86-00513R001755120009-1"

TAUC, J.

"Determination of the Optical Activation Energy of Germanium by the Method of Photoelectric Lines." p. 256,
(CESKOSLOVENSKY CASPIS PRO FYSIKU, Vol. 4, No. 3, June 1954, Praha, Czechoslovakia)

SO: Monthly List of East European Accessions, (EEAL), LC, Vol. 4
No. 5, May 1955, Uncl.

~~FACT, TAUC, JAN~~

These are given in Table I. The optical activation energy of Be might be equal to the width of the band of forbidden energy values ($0.76 - 4 \times 10^{-4} T$ ev., where T is abs. temp.). A Fe junction, prep'd according to Teal, *et al.* (*Phys. Rev.* 81, 837 (1951)), is illuminated obliquely with a radiator according to Abraham (*Fys. Medd.* 2, 14 (1954)) at 233° or 204°K. The black-body radiation is interrupted by means of a rotating sector about 1000 times per sec. and the resulting potential is measured with a vacuum-tube voltmeter, compared to a const. amplitude signal. At 204°K measured with a ^{90}Sr thermocouple the optical activation energy is 0.62 ± 0.02 ev. Manfred Maunziner

J
CZECH

3763. The photo-electric properties of indium anti-
monide. J. UHL AND A. ABRAHAM. Czech J. Phys.
3, No. 8-9, 1953, p. 344.

Change of resistance in the formation of a
voltage in a non- or polycrystalline sample of InSb.
Due to illumination has been observed the magnitudes
of which increase with decreasing temperatures.

Change in the volume of the sample or at barriers due
to non-homogeneities, and a photo voltaic effect. The
spectral curves were measured with long-wave limits
($\lambda = 5.8 \mu$ at $155^\circ C$, $\lambda = 6.7 \mu$ at $42^\circ C$). It
is shown that these phenomena are caused by the
removal of electrons from the valence-band. The
photoelectric current under the influence of light is
proportional to λ^{-1} .

Activation temperature was found to be $E_a =$
 $0.24 - 2.4 \times 10^{-3} T$ (eV).

BD *getta*

TAUC, J.

Zdenek Matyas' Uvod do Kvantove fysiky polovodnicu (Introduction to the Quantum Physics of Semiconductors): a book review p. 589.
SALEOPROUDY OBZOR, Vol. 15, No. 12, Dec., 1954, Prague.

SO: Monthly List of East European Accessions, (EEAL), LC, No. 5, No. 6, June, 1956, Uncl.

TAUC, J.

"Dynamics of the electrons in an ideal crystal lattice."

The aim of the paper is to give sufficiently detailed explanation of the conceptions used in modern physics for explaining phenomena which occur in germanium and silicon rectifiers, transistors, phototubes, etc., by J. Tauc.

SO: ELEKTROTECHNICKY OBZOR (Electrical Engineering Review, Czechoslovakia)
Vol. 43, No. 2, Feb., 1954

TAUC, J.

Crystal lattice defects and their effect upon the electric properties of semiconductors. p. 421. ELEKTROTECHNICKY OBZOR. (Ministerstvo strojirenstvi a Ministerstvo paliv a energetiky) Praha. Vol. 43, no. 8, Aug. 1954.

SOURCE: East European Accessions List, Vol. 5, no. 9, September 1956

TAUC, J.

Theory of circumferential photovoltaic phenomenon in semiconductors. p.34
CESKOSLOVENSKY CASOPIS PRO FYSIKU Vol. 5, No. 1, Jan. 1955

SO: Monthly East European Accession List (EEAL), LC, Vol. 4, No. 9, Sept. 1955, Uncl.

100 V C

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1950 the theory of a bulk photo voltaic phenomenon
is based on the effect of a semiconductor with a
photo voltaic theory [1947] or at a $p-n$ junction
[Stern, 1947]; but the presence of non-rectifying
contacts [Dember's phenomenon, Leshkevich's theory
(1948)] is necessary. The case is considered that the
illuminated part of the semiconductor is sufficiently
distant from both contacts so that these will not assert
themselves; further, it is assumed that there are no
localized potential barriers in the semiconductor.
Under these conditions a photovoltage is produced
in a semiconductor if its conductivity varies through-
out its length in such a way that in the dark it is
different at the beginning and end of the illuminated
part. For this type of "non-barrier and non-contact"
photovoltage the name "bulk" photovoltage is pro-
posed. The underlying law of this phenomenon, the
general procedure for calculating the photovoltage, an
approximation for weak illumination and the depen-
dence on the intensity of illumination are derived and
its physical aspects are discussed.

now get

TAUC, J.

TAUC, J. Thermodynamics of "nonbarrier" photovoltaic phenomena barriers.
p. 251.

Vol. 5, no. 3, May 1955
CESKOSLOVENSKY CASOPIS PRO FYSIKU
SCIENCE
Praha, Czechoslovakia

So: East European Accessions, Vol. 5, no. 5, May 1956

TAVC, J.

337.312.5 : 337.311.33
9670. The thermodynamics of non-barrier-layer
photovoltaic phenomena. J. TAVC, Czech. J. Phys.,
5, No. 3, 300 (Aug., 1955).

By using quasi-Fermi levels introduced by Shockley,
which have the meaning of partial chemical potentials
of an assembly of electrons and an assembly of holes,
and an analogy with galvanic cells, an equation was
derived for the photovoltage of a non-barrier-layer
semiconductor photocell on the basis of thermo-
dynamic laws. For the case that classical statistics
are valid the basic equation leads to the result derived
by kinetic considerations. Attention is thus drawn
to the application of thermodynamics to photovoltaic
phenomena in semiconductors.

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CIA-RDP86-00513R001755120009-1"

WANG, S.

Physics of semiconductors. p. 489.

CESKOSLOVENSKY CASOVIK PRO FYZIKU vol. 5, no. 5, Sept. 1955

Czechoslovakia

so. EAST EUROPEAN ACCESSIONS LIST vol. 5, no. 7 July 1956

TAUC, J.

Thermal photoelectric phenomenon in semi conductors. p. 614

Vol. 5, no. 6, Nov. 1955
CESKOSLOVENSKY CASOPIS PRO FYSIKU
Praha, Czechoslovakia

So: Eastern European Accession Vol. 5, No. 4, 1956

TAUC, Jan

Category : CZECHOSLOVAKIA/Electricity - Semiconductors

G-3

Abs Jour : Ref Zhur - Fizika, No 2, 1957, No 4162

Author : Tauc, Jan

Inst : Ustav techn. fys. CSAV, Prague, Czechoslovakia

Title : Electronic Phenomena in Semiconductors with a Temperature Gradient.

Orig Pub : Ceskosl. casop. fys., 1956, 6, No 2, 132-146

Abstract : A theoretical investigation is made of the phenomena involved in the transfer of current carriers as a result of a temperature gradient in semiconductors with two types of current carriers. General equations are introduced for the carrier concentration and for the density of the electric and thermal currents. On the basis of these equations, expressions are obtained for the distribution of the concentration of the electrons and holes in the semiconductor. An expression is derived for the current produced in the presence of a temperature gradient; this current can be interpreted as the emission of negative current carrier from the points with higher temperatures. The dependence of the thermal emf on the temperature gradient is calculated. The phenomenon of temperature rectification is investigated and it is shown that this rectification is insignificant.

Card : 1/1

Tauc, J.

All-Union conference on the physics of semiconductors in Leningrad.
P. 232
CESKOSLOVENSKY CASOPIS PRO FYSIKU. (Ceskoslovenska akademie ved.
Ustav technicke fysiky) Praha
Vol. 6, no. 2, Mar. 1956

Source: EEAL - LC Vol. 5. No. 10 Oct. 1956

TAUC J.

INDUCTION IN A METAL ROTATING IN A HOMOGENEOUS MAGNETIC FIELD
J. Tauc
J. Phys., Vol. 6, no. 5, 421-4 (Oct., 1946)

The e.m.f. induced in a metal rotating in a homogeneous magnetic field is calculated. It is shown that this e.m.f. is composed of two parts — bulk and boundary. Results are given of experiments carried out on iron, aluminum, and copper, all of which the conclusions of the theory were verified.

1/2 30x
H.L.

TAUC, J.; DRAHOUPIL, J.; MALKOVSKA, M.

Quantum effect of photoelectric phenomenon in germanium in X-ray radiation. p. 21.
(Ceskoslovensky Casopis Pro Fysiku. Vestnik. Vol. 7, no. 1, 1957.)

SO: Monthly List of East European Accession (EEAL) LC, Vol. 6, no. 7, July 1957. Uncl.

"APPROVED FOR RELEASE: 07/16/2001 CIA-RDP86-00513R001755120009-1

APPROVED FOR RELEASE: 07/16/2001 CIA-RDP86-00513R001755120009-1"

TAUC, J.

International Conference on Semiconductors and Phosphors in Garmisch-Partenkirchen.
p. 111. (Ceskoslovensky Casopis Pro Fysiku. Vestnik. Vol. 7, no. 1, 1957.)

SO: Monthly List of East European Accession (EEAL) LC, Vol. 6, no. 7, July 1957. Uncl.

Tauc Jan

CZECHOSLOVAKIA/Electricity - Semiconductors

0-3

Abs Jour : Ref Zhur - Fizika, No 5, 1958, No 11036

Author : Tauc Jan

Inst : Not Given

Title : Fraction of Thermal Energy Taken from the Surrounding Medium
in the Electroluminescent Energy Radiated from a p-n Junction

Orig Pub : Ceskosl. casop. fys., 1957, 7, No 3, 246-247

Abstract : See Referat: Zhur Fizika, 1958, No 2, 3812

Card : 1/1

TAUC JAN.

CZECHOSLOVAKIA/Electricity - Semiconductors

G-3

Abs Jour : Ref Zhur - Fizika, No 5, 1958, No 11048

Author : Tauc Jan

Inst : Not Given

Title : Remark Concerning the Theory of Anomalous Thermal Electric Phenomenon in Semiconductors

Orig Pub : Chekhosl. fiz. zh., 1957, 7, No 3, 376-377

Abstract : See Referat: Zhur Fizika, 1958, No 5, 11047

Card : 1/1

TAC, J.

AUTHORS: Šanc, J. and Abraham, A.
 TITLE: The Quantum Efficiency of the Interband Photoelectric valence
 Effect in Indium Antimonide (Avantová Minrost vnitřního
 fotoelektrického jevu v antimikdó Indiu v antimonu)

PERIODICAL: Československý Casopis Pro Fyziku, 1958, Nr. 6,
 Vp 653 - 657 (Czech)

ABSTRACT: The quantum efficiency η of the photoelectric effect in
 germanium is approximately unity for all quanta whose
 energy E lies between E_1 and E_2 for $E_1 > E > E_2$.
 The quantum efficiency rises above unity (Refs. 1, 2) and
 falls in explained by collision between the fast
 electrons produced by the absorption of high-energy quanta
 in the valence band (Ref. 3). Measurements
 of the photoelectric effect on a P-N junction (Ref. 4). These
 measurements are carried out by determining (Ref. 4) the
 photoelectric effect on a P-N junction (Ref. 4). These
 cannot be prepared sufficiently reliably in InSb and
 therefore the photo-conductivity and the photo-electro-
 conductivity (PME) effect have been measured in InSb. The
 magnetic (PME) effect has been measured in pairs of
 free carriers, while the photo-conductivity may be
 influenced by barriers, traps, etc.
 The PME effect decreases with decreasing absorption
 according to $\eta \propto 1$ (Ref. 5). On the
 other hand, the photo-conductive signal decreases with
 increasing absorption coefficient according to $\eta \propto (2 -$
 $\eta_0)$. The measurement of both effects enables one to
 find η_0 (Ref. 6) and to eliminate its influence on the
 measurement of the infra-red illumination used for the
 measurement was interrupted at a frequency of 63 cps.
 The intensity of the light was measured with a thermopile
 and the signal from the sample was amplified with a
 narrow-band amplifier and measured with a valve voltmeter.
 The sample was mounted in a cryostat in a magnetic field
 of 3,500 - 6,500 Gauß. The results quoted were obtained
 from polycrystalline specimens with $6.4 \times 10^4 \text{ cm}^{-2}$
 acceptor and a shallow Al_2O_3 cleavage at room temperature
 $\eta = 4.6 \times 10^4 \text{ cm}^2 \text{ V}^{-1} \text{ sec}^{-1}$

The contacts were soldered on with indium. The samples
 were electrolytically etched (Ref. 7). They were 0.05 to
 0.2 mm thick and their resistance at room temperature was
 1 to 15 Ω .
 Figure 1 shows the dependence of the quantum efficiency
 as a function of the energy of the absorbed photons, i.e.
 the PME effect at 18°C. Figure 2 shows the
 same quantity measured at -64°C. The curves show
 measurements of the PME effect. Both graphs are normalized so that
 the quantum efficiency is unity in the vicinity of the
 absorption edge (Ref. 6). Measurements of photo-conductivity
 could not be made at room temperature because the antennae
 were very small and the bolometric effect distorted the
 results. To eliminate a further possible error, the
 reflection coefficient was also studied and found to be
 constant over the range of wavelengths used.
 All the measurements remained constant until the wavelength
 up to $\lambda \approx 0.47 \text{ } \mu$ and started to rise at this wavelength.
 The rise slowed down and η became independent of wavelength
 again, though at a slower and apparently constant rate.
 η_1 and η_2 were dependent on the sample, particularly

Czech/5

CECRL/77-58-6-10
The Quantum Efficiency of the Internal Photoelectric Effect in
Intrinsic Antimony
on the structure of its surface and on the temperature, but
the type of dependence was reproducible. Because the
curves derived from the PPE effect practically coincide
with those derived from measurements of photo-conductivity,
one may safely conclude that indeed it is the number of
pairs of holes and electrons, produced by the number of
quanta, which is shown in the figures. The energy
 $E_1 - E_0$ = 1.6 E_0 , which is
for ionisation by collision (Ref 9, 10). The authors
show a roughly estimated one-dimensional (K) diagram
for E_0 which would explain the observed behaviour.
Point E_1 occurs when the holes acquire sufficient energy
else to produce ionisation.
Landsberg (Ref 11) has recently suggested that a rise of
the quantum efficiency with increasing energy of the
absorbed photons might help to resolve certain of the
difficulties found by the authors in the right direction,
but not sufficiently large. There are 4 figures and
11 references, 7 of which are English, 4 German, 1 Czech, 1 French.
ASSOCIATION:
Data Techniques Faculty CSAV, Prague
(Institute of Technical Physics of the Czech Ac.Sc.,
Prague)

CZECH/37-59-3-3/29

AUTHORS: Tauc, Jan and Závětová, Milena

TITLE: Photo-piezoelectric Effect in Semiconductors

PERIODICAL: Československý časopis pro fysiku, 1959, Nr 3, pp 241-245

ABSTRACT: The conditions for the occurrence of a photo-voltaic effect have recently been studied by the author, J. Tauc (Ref 1,8). A basic condition is some inhomogeneity in the semiconductor. In Ref 1, it has been shown that if the width of the forbidden band changes along the illuminated region from E_{Gb} to E_{Gc} , then an e.m.f. given by:

$$U = - \frac{1}{e} \Delta T_1 (E_{Gc} - E_{Gb}) \quad (1)$$

arises $\Delta T_1 = \sigma_1/\sigma - \sigma_0/\sigma_0$ where σ is the total conductivity of the illuminated sample, σ_0 the dark conductivity and σ_1 and σ_{10} relate to the conductivities of the electrons in the conduction band. The width of the forbidden band in a semiconductor depends on pressure (W. Paul and D.M. Warschauer - Refs 2,3) and Price (Ref 4) ✓

Card1/4

Photo-piezoelectric Effect in Semiconductors CZECH/37-59-3-3/29

has suggested that a photo-voltaic effect might be observed in an inhomogeneously stressed semiconductor. The measurements were carried out on single crystals of n-type germanium ($\rho = 30 \Omega \text{ cm}$ at room temperature), p-type germanium ($\rho = 12 \Omega \text{ cm}$) and on p-type silicon ($\rho = 570 \Omega \text{ cm}$). The samples were cut perpendicular to (111) and their dimensions were $1 \times 1 \times 15 \text{ mm}$. They were etched in CP4. The contacts were made with a gallium and zinc eutectic by a method worked out by Trousil. The illuminated area was $0.2 \times 1 \text{ mm}$ and the sample could be moved along the light-spot. The pressure was applied by two edges. The sample was compressed between them and the force was measured. The maximum pressure that could be applied without mechanically damaging the samples was 4000 kg/cm^2 and it acted on an area $0.2 \times 1 \text{ mm}$. Measurements were made either with chopped light and AC amplification or with constant illumination and a galvanometer.

Card2/4

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CZECH/37-59-3-3/29

Photo-piezoelectric Effect in Semiconductors

Because most samples showed a photo-e.m.f. even without pressure, this was first plotted as a function of the location of illumination. The same function was then plotted while pressure was applied to the sample. The photo-piezoelectric e.m.f. was the difference between the two curves. It is plotted, for a sample of p-type silicon, in Figure 2 as a function of position of illumination and in Figure 3 as a function of pressure.

The sign of the e.m.f. follows from Eq (1) after inserting:

$$\Delta t_1 = \frac{1}{1 + \mu_1/\mu_2} \cdot \frac{\Delta \sigma}{\sigma}$$

for n-type semiconductors, or:

$$\Delta t_1 = \frac{1}{1 + \mu_2/\mu_1} \cdot \frac{\Delta \sigma}{\sigma} \quad \checkmark$$

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Photo-piezoelectric Effect in Semiconductors CZECH/37-59-3-3/29

for P-type semiconductors.

Here μ_1 and μ_2 are the mobilities of electrons and holes, respectively, and $\Delta\sigma$ is the change in conductivity due to illumination. Table 1 gives the sign of the e.m.f. for the illuminated end of the sample. This is an agreement with the measurements. The observed effect is of the order of magnitude that was expected theoretically. Eq (1) is proved in an appendix. There are 4 figures, 1 table and 10 references, of which 3 are Czech and 7 English.

ASSOCIATION: Ústav technické fysiky ČSAV, Praha (Institute of Technical Physics, Czechoslovak Ac.Sc., Prague)

Card 4/4

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TAUC, JAN

Electron Impact Ionization in semiconductors. J. Tauc
(Czechoslovak Acad. Sci., Prague). *Phys. and
Solids* 8, 219-23 (1959).--A review of expts. concerning the
quantum yield of the inner photoelec. effect and its de-
pendence on the photon energy. The theory appropriate
to these phenomena is discussed. J. M. Hossig

Distr: 4E3c/4E3d

2
2

TAUC, JAN

The quantum efficiency of the internal photoelectric effect in indium antimonide, Jan Tauc and Antonin Abramov (Czechoslov. Acad. Sci., Prague). *Czechoslov. J. Phys.* 9, 95-100 (1959) (in English).—A method is described for measuring the relative quantum efficiency of the internal photoelec. effect in semiconductors by simultaneously measuring the photomagnetic and photoconductive effects. The results of measurements on InSb are given. The quantum efficiency begins to increase if the energy of the photon exceeds 0.47 e.v. at room temp. The quantum efficiency as a function of the energy of the photon is analyzed in terms of impact ionization, and it is shown that a study of the structure of this curve can supply information on the band structure of a semiconductor in the region of high energies of electrons and holes. A. Kremel

abt
11

1E30

2-4E30

1-RS

3

TAUC, J.

Distrs: 4E1x(g)/4E2d(b) 2 cys;
Photopiezoelectric effect in semiconductors. Jan Tauc
and Milena Zvárová (Czechoslov. Acad. Sci., Prague).
Czechoslov. J. Phys. 9, 573-7 (1959) (in English).—A new
photoelastic effect was observed which is caused by the
nonhomogeneous distribution of pressure in a semiconductor.
Its origin can be explained by considering the dependence of
the energy gap on the pressure. A. Kremkeller

4
1-JAT (MAY)
1-ZTP(G)
3

TAUC, J.

1 The high-voltage photoeffect in ZnS single crystals.
2
J. Tauc (Czechoslovak Acad. Sci., Prague). *Phys. and
Chem. Solids* 11, 345-6 (1959).—The recently observed
photovoltaic effects are ascribed to the presence of stacking
faults at points where cubic and hexagonal domains meet.
It is assumed that the photoeffect in the barriers decreases
sharply with wave length and that a concn. gradient of
donors in each structure generates internal barriers.

J. McHennig

M.
gt

TAUC, J.

Karel Smirous; an obituary. Cs cas fys 11 no.6:556 '61.

1. Ustav technicke fysiky, Ceskoslovenska akademie ved, Praha.

(Smirous, Karel) (Physics)

TAUTS, Ya. [Tauc, Jan], prof.; MIKHAYLOVA, M.P. [translator];
KOLOMIETS, B.T., red.; TELESNIN, N.L., red.; REZOUKHOVA,
A.G., tekhn. red.

[Photoelectric and thermoelectric effect in semiconductors]
Foto- i termoelektricheskie iavleniya v poluprovodnikakh.
Pod red. B.T.Kolomiitsa. Moskva, Izd-vo inostr. lit-ry,
1962. 250 p. (MIRA 16:5)

(Semiconductors)

TAUC, J.

International Conference on Strong Magnetic Fields. Cs cas fys
12 no. 2:199-201 '62.

1. Ustav fysiky pevných látok, Československá akademie vied, Praha.

TAUC, Jan

The first Czechoslovak semiconductor laser, Vestnik ČSAV 72
no.5:600-601 '63

L 21318-66 EWP(t) IJP(c) JD
ACC NR: AP6003658

SOURCE CODE: CZ/0055/65/015/010/0730/0739

AUTHOR: Tauc, J.; Abraham, A.

ORG: Institute of Plasma Physics, Czechoslovak Academy of Sciences, Prague

62
B

TITLE: Optical properties and band structure of CdSb

SOURCE: Chekhoslovatskiy fizicheskiy zhurnal, v. 15, no. 10, 1965, 730-739

TOPIC TAGS: cadmium compound, antimonide, photon, valence band, conduction band

ABSTRACT: In continuing the experimental studies of the structure of the absorption edge of cadmium antimonide recently carried out by M. Zavetova (Czech. J. Phys. B 14 1964, 615), the present paper deals with a detailed study of the region of direct transitions adjoining the region of indirect transitions. In the experiment the optical constants of CdSb were determined for photon energies up to 2 eV from reflectivity measurements and by using the Kramer-Kronig dispersion relation. The experimental set-up for the reflectivity measurements is described. Possible locations of the observed direct transitions are found by the application of the selection rules. It is shown how these results, together with those regarding the transport properties of CdSb, can be used to obtain information about the structure of the valence and conduction bands. [The authors thank A. Hruba for the preparation of the samples, M. Silhava and M. Sulova for help with the measurements and computations, and V. Frei and B. Velicky for many helpful discussions.] Orig art. has: 7 figures, 1 table, and 1 formula.

Card 1/2

L 21318-66

ACC NR: AP6003658

SUB CODE: 20, 11/ SUBM DATE: 07Jun65/ ORIG REF: 008/ OTH REF: 004/
SOV REF: 002/

Card 2/2

L 36856-66 T/EW(t)/ETI IJI(c) JD
ACC NR: AP6019274 SOURCE CODE: GE/0030/66/015/002/0627/0637 46
AUTHOR: Tauc, J.; Grigorovici, R.; Vancu, A. 43
B
ORG: [Tauc] Institute of Solid State Physics of the Czechoslovak
Academy of Sciences, Prague; [Grigorovici; Vancu] Institute of Physics
of the Rumanian Academy of Sciences, Bucharest
TITLE: Optical properties and electronic structure of amorphous
germanium 1
SOURCE: Physica status solidi, v. 15, no. 2, 1966, 627-637
TOPIC TAGS: amorphous germanium, electronic structure, optic property,
energy dependence, optic density
ABSTRACT: The optical constants of amorphous Ge are determined for
photon energies from 0.08-1.6 eV. From 0.08-0.5 eV, the absorption
is due to k-conserving transitions of holes between the valence bands
as in p-type crystals; the spin-orbit splitting is found to be 0.20
in non-annealed, and 0.21 eV in annealed samples. The effective
masses of the holes in the three bands are 0.49 m, 0.04 m, and 0.08 m.
An absorption band is observed below the main absorption edge (at
300K; the maximum of this band is 0.86 eV); the absorption in this
band increases with increasing temperature. This band is considered
Card 1/2

L 36856-66

ACC NR: AP6019274

to be due to excitons bound to neutral acceptors, and these are presumably the same ones that play a decisive role in the transport properties and which are considered to be associated with vacancies. The absorption edge has the form: $\omega^2 \epsilon_2 \sim (\hbar \omega - E_g)^2$ 3

($E_g = 0.88$ eV at 300K). This suggests that the optical transitions conserve energy, but not the k vector, and that the densities of states near the band extrema have the same energy dependence as in crystalline Ge. A simple theory describing this situation is proposed, and comparison of it with the experimental results leads to an estimate of the localization of the conduction-band wave functions. For the suggested interpretation of the experimental results, the authors profited very much from discussions with Dr. E. Antoncik and Dr. B. Velicky; fruitful discussions with Dr. L. Banyai and also acknowledged. Orig. art. has: 4 figures and 14 formulas. [Authors' abstract.] [KS]

SUB CODE: 20/ SUBM DATE: 25Feb66/ ORIG REF: 005/ OTH REF: 001

ms
Card 2/2

HANCIL, Jan, ins.; TAUCHMAN, Vlastimil

Operational experience with the superfiner in making trunk
fiberboard. Papir a celulcsa 19 no.2:39-40 F'64.

1. Krkonoske papirny, Hostinne.

RIPKA, Otto, MUDr.; TAUER, Emil, MUDr.

Three years of experience in ambulant therapy of sixty hypertonics with pentamethonium. Vnit. lek., Brno 1 no.10: 767-776 Oct 55.

1. Z druhe vnitri kliniky KU v Praze, prednosta prof. Dr. A. Vancura II. vnitri klinika, Praha II. U nemocnice 2.

(HYPERTENSION, therapy

pentamethonium, ambulant treatment.)

(MUSCLE RELAXANTS, ther. use

pentamethonium in hypertension, ambulant treatment.)

TAUER, J.

"The spark plug in a gas engine," p. 21 (MOTORYZACJA, Vol. 8, no. 1, Jan. 1953,
Warszawa, Poland)

SC: Monthly List of East European Accessions, Vol. 2, #8, Library of Congress
August, 1953, Unclassified.

Z/028/80/000/002/004/005
D253/D304

AUTHOR:

Tauer, Jaroslav

TITLE:

What do we understand by the term "exosphere"?

PERIODICAL:

Pokroky matematiky, fysiky a astronomie, no. 2, 1980,
185-186

TEXT: The author defines the term "exosphere" and lists some characteristics of this outermost layer of the atmosphere. The information contained in this article is compiled from Western sources exclusively. According to Kato and Watanabe (Ref. 1: The Science Reports of the Tôhoku University, Fifth Series, Geophysics, Vol. 10, No. 3, 1959 (119-120)), the outermost atmosphere or exosphere is "the interplanetary gas enclosed in a cavity (as proposed by Chapman and Ferraro) which is formed by the relative motion between the earth and the stream of solar corpuscles, or between the earth and the interplanetary matter under the influence of terrestrial rotation." Storey (Ref. 2: Phil. Trans. Roy. Soc., A 246, 1953, (113)) refers to "whistling atmospherics" and estimates ion concentrations in the order of $10^4 - 10^3$ particles/cm³ at altitudes from 1,500 km to several thousands of

Card 1/3

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Z/028/60/000/002/004/005
D253/D304

What do we understand...

km. These ion concentrations and those listed by other authors are in good agreement with geomagnetic and cosmic observations. The border zone between the exosphere as the outermost region of the atmosphere and interplanetary space is situated at an altitude of 8-9 earth radii. The ion concentration in this zone increases rapidly, which produces a double effect: (1) Inside the border zone, the rotation of the magnetic field causes eddy currents which shield the interplanetary space from influences of the terrestrial magnetic field; (2) From outside the border zone, the kinetic pressure of particles acts; this is equal to the pressure of the magnetic field and thus prevents particles in the interplanetary space from being dragged into rotation with the earth. According to this model, the geomagnetic field is in a sort of cavity, enclosed by induction currents, and its outer limit of influence is changed only by heavy impacts of solar corpuscles during periods of increased activity, e.g., eruptions. These changes then provoke the well-known geomagnetic storms. There are 1 figure and 5 references. The references to the four most recent English-language publications read as follows: Kato, Watanabe: The Science Reports of the Tohoku University, Fifth Series, Geophysics, Vol. 10, No. 3, 1959 (119-120); Obayashi: Report of Ionosphere Research in Japan, Vol. XII, No. 3, 1958 (316); Helliwell: ✓

Card 2/3

What do we understand...

Z/028/60/000/002/004/005
D253/D304

Low Frequency Propagation Studies, Part I, AFCRC-TR-56-189, Univ. Stanford,
1958; Siedentoph, Behr: Zs. Astrophys., 32, 1953.

ASSOCIATION: Geofysikální ústav ČSAV, Praha (Geophysical Institute of the
Czechoslovak AS, Prague)

✓

Card 3/3

TAUER, Jaroslav

On methods used for determining the effect of solar eclipse on
the geomagnetic field. Studia geophys 8 no.1:72-81 '64.

1. Geophysical Institute, Czechoslovak Academy of Sciences,
Praha 4 - Sporilov, Bocni II.

TAUER, Jaroslav

A hydromagnetic model of the solar eclipse effect on the diurnal variation of the geomagnetic field. *Studia geophys* 8 no. 3:314-316 '64.

1. Institute of Geophysics, Czechoslovak Academy of Sciences,
Prague 4 - Sporilov, Boční II.

"APPROVED FOR RELEASE: 07/16/2001 CIA-RDP86-00513R001755120009-1

APPROVED FOR RELEASE: 07/16/2001 CIA-RDP86-00513R001755120009-1"

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CIA-RDP86-00513R001755120009-1

Card 3 / 3

APPROVED FOR RELEASE: 07/16/2001

CIA-RDP86-00513R001755120009-1"

TAUER, L.M., inzhener

Continuous operation method of placing trestles for railroad bridges.
Transp. stroi. 5 no. 6:27-28 Ag'55. (MIRA 8:12)
(Railroad bridges)

TAUER, L. M.

Tauer, L. M.

"The suspended assembly of the span structures of steel bridges. The problem of the economy of suspended assembly of steel bridges." Min Higher Education USSR. Moscow Order of Labor Red Banner Construction Engineering Inst imeni V. V. Kuybyshev. Moscow, 1956. (Dissertation for the Degree of Candidate in Technical Sciences.)

Knizhnaya letopis'
No. 15, 1956. Moscow.

TAUER, L.M.

Erection of the all-welded span of the Novo-Arbatskii bridge.
Transp. stroi. 8 no.8:20-22 Ag '58. (MIRA 11:10)

1. Nachal'nik montazhnogo uchastka mostootryada No.4.
(Moscow--Bridges--Welding)

TAUER, L.M., kand.tekhn.nauk

*Floating the span-bridge construction elements over the
Moskva River in Luzhniki. Transp.stroi. 9 no.10:23-27
0 '59. (MIRA 13:2)*
(Luzhniki--Bridges, Concrete)

TAUER, L.M., kand. tekhn. nauk

Modern tendencies in bridge construction abroad. Transp.
stroi, 12 no.1:54-58 Ja '62. (MIRA 17:2)

TAUER, L.M., kand.tekhn.nauk

Efficient design of large-span reinforced concrete bridges. Avt.
dor. 25 no.7:25-26 Jl '62. (MIRA 15:8)
(Bridges, Concrete—Design)

"APPROVED FOR RELEASE: 07/16/2001 CIA-RDP86-00513R001755120009-1

APPROVED FOR RELEASE: 07/16/2001 CIA-RDP86-00513R001755120009-1"

TABLE

2264

Use of chlorine dioxide. II. Titration in glacial acetic acid. S. Skramzovsky, Z. Tauer, and J. Novotny (Karlova Univerzita, Prague). *Czech. Listy* 49, 141 (1955); cf. *C.A.* 49, 7814. ClO_2 is suitable for potentiometric titrations of I^- and for detns. of I^- in the presence of Br^- and Cl^- in anhyd. AcOH . The titer of ClO_2 is detd. with quinol. Potential of the ClO_2/Cl^- system in 0.05M H_2SO_4 and in AcOH is +480 mv, and in 0.1M NaOAc +700 mv. Detn. of I^- was successful even with 8 mg. KI in the presence of 2.5 mg. Cl^- or 3.5 mg. Br^- in 10 ml. AcOH . M. Hudlicky.

TAUER, Z.

Distr: 4E3d

Reactions of radicals or excited water molecules in traces of ionizing particles. Z. Tauer, F. Duhačký, and J. Bednář (Vojenská akad. A. Zapotockého, Brno, Czech.). Collection Czechoslov. Chem. Commun. 25, 1221-6 (1960). The yields of nitrite were measured in nitrate solns. irradiated by β -radiation. In these solns. nitrite is formed by an indirect action of radicals or excited water mols. and by the direct radiation action on nitrate ions. The effect of pH on nitrite yield is explained by secondary reactions. B. Erdos

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1 BW(BW)

1 JPT(DH)

"APPROVED FOR RELEASE: 07/16/2001

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APPROVED FOR RELEASE: 07/16/2001

CIA-RDP86-00513R001755120009-1"

TAUFEL, K.

The training of chemists for the food industry . Tr from the German. p. 217.
(Prumysl Potravin, Vol. 8, No. 4, 1957, Praha, Czechoslovakia)

SO: Monthly List of East European Accessions (EEAL) LC, Vol. 6, No. 8, Aug 1957. Uncl.

TAUFEL, K.

Studies on saturated fatty acids under the influence of high energy
radiations. Cesk. gastroent. vyz. 16 no.3/4:314-315 Ap '62.
(FATTY ACIDS) (ULTRAVIOLET RAYS)
(RADIATION EFFECTS)

TAUFER, J.

Standard drilling machinery for quick clamping, p. 106

STROJNISKE VESTNIK (Fakuleta za elektrotehniko in strojnistro Univerze v Ljubljani Institut za turbostroje v Ljubljana Drustvo strojnih inženirjev in tehnikov LR Slovenije in Storjna industrija Slovenije) Ljubljana, Yugoslavia. Vol 4, no. 3/4, June 1958

Monthly List of East European Accession EEAIC, Vol. 8, no. 6, June 1959
Uncla.

TAUFER, J.

TECHNOLOGY

TAUFER, J. Devices for pneumatic clamping. 154

Vol. 4, no. 6, Nov. 1958

Monthly List of East European Accessions (FEAI) LC, Vol. 8, no. 3
March 1959 Unclass

TAUFER, J.

Examples of pneumatic clamping holders. p. 136.

STROJNISKI VESTNIK. (Fakulteta za elektrotehniko in strojninstvo Univerze v Ljubljani, Institut za turbostroje v Ljubljani, Drustvo strojnih inzenirjev in tehnikov IR Slovenije in Strojina industrija Slovenije)
Ljubljana, Yugoslavia
Vol. 5, no. 4/5, Aug., 1959

Monthly list of Eastern European Accession Index (EEAI) IC vol. 8, No. 11
November 1959
Uncl.

TAUFER, Janez

Pneumatic drill. Stroj vest 6 no.2:77-78 Mr '60.
(Boring machinery)
(Pneumatic tools)

(EEAI 9:10)

TAUFER, Janez

Pneumatic turning device. Stroj vest 6 no.3:116 M6 '60. (EEAI 10:1)

1. Tovarna avtomobilov Maribor
(Pneumatic machinery) (Turning)

TAUFER, Janez (Maribor)

Equipment for center turning. Stroj vest 7 no. 4-5:144-146 0 61.

1. Tovarna avtomobilov in motorjev, Maribor.

TAUFER, Janez

Clamping devices for the dents in stamping machines. Stroj vest 8
no.4/5:108-110 0 '62.

1. Tovarna avtomobilov in motorjev, Maribor.

TAUPER, Janez

Pneumatic jigs. Stroj vest 10 no.3:77 Je '64.

1. Maribor Automobile and Engine Factory, Maribor.

TAUPROVA, M., MIHATSKY, Z.

Public health personnel in Czechoslovakia. Zdravot. rev. 25:6,
June 50, p. 144-8

CLML 19, 5, Nov., 1950

TAUFROVA, M. MUDr.

Work of the district physician in the fields of hygiene & epidemiology.
Cesk zdravot 6 no.7:355-360 July 58.

1. Vyzkumny ustav organisace zdravotnictvi.

(PUBLIC HEALTH

in Czech., relation of district physician to hyg. &
epidemiol.(Cz))

(EPIDEMIOLOGY

in Czech., relation of district physician (Cz))

(HYGIENE

same)